HEF40240B

Octal inverting buffers with 3-state outputs Rev. 5 — 15 November 2011

Product data sheet

1. **General description**

The HEF40240B is an octal inverting buffer with 3-state outputs. It features output stages with high current output capability suitable for driving highly capacitive loads.

The 3-state outputs are controlled by the output enable inputs nOE. A HIGH on nOE causes the outputs to assume a high-impedance OFF-state. The device also features hysteresis on all inputs to improve noise immunity. Schmitt-trigger action makes the inputs highly tolerant to slow input rise and fall times.

The HEF40240B is pin and functionally compatible with the TTL '240' device.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD}, V_{SS}, or another input.

Features and benefits 2.

- Tolerant of slow input rise and fall times
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Specified from -40 °C to +85 °C
- Complies with JEDEC standard JESD 13-B

Ordering information

Table 1. **Ordering information**

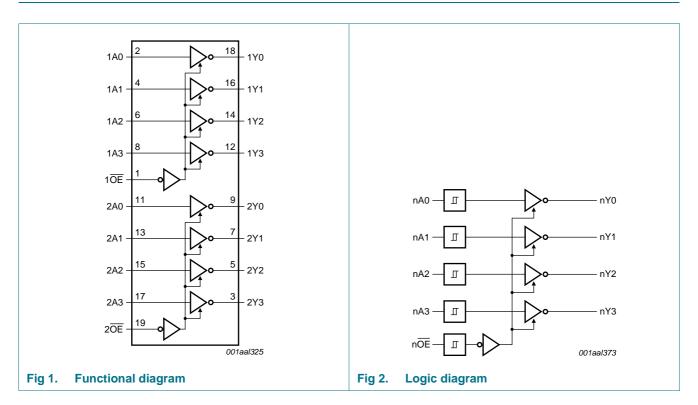
All types operate from -40 °C to +85 °C.

Type number	Package								
	Name Description								
HEF40240BP	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1						
HEF40240BT	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1						



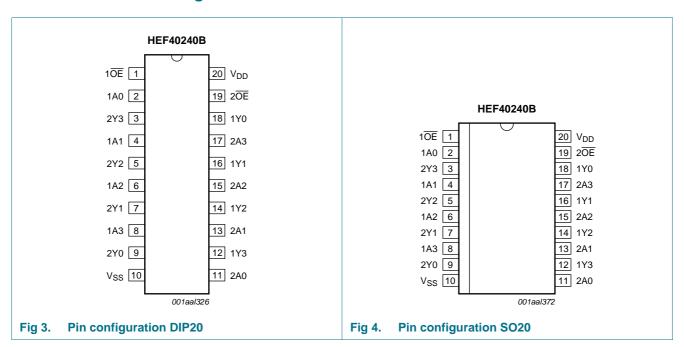
Octal inverting buffers with 3-state outputs

4. Functional diagram



5. Pinning information

5.1 Pinning



Octal inverting buffers with 3-state outputs

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1 OE	1	output enable input (active LOW)
1A0, 1A1, 1A2, 1A3	2, 4, 6, 8	data input
V _{SS}	10	ground (0 V)
2Y0, 2Y1, 2Y2, 2Y3	9, 7, 5, 3	data output
2A0, 2A1, 2A2, 2A3	11, 13, 15, 17	data input
V_{DD}	20	supply voltage
1Y0, 1Y1, 1Y2, 1Y3	18, 16, 14, 12	data output
2 OE	19	output enable input (active LOW)

6. Functional description

Table 3. Function table[1]

Inputs nAn	Output	
nAn	nOE	nYn
Н	L	L
L	L	Н
X	Н	Z

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$	-	±10	mA
V_{I}	input voltage		-0.5	$V_{DD} + 0.5$	V
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{DD} + 0.5 \text{ V}$	-	±10	mA
I _I	input leakage current	into any input	-	±10	mA
lo	output current	sink or source current	[1] -	±25	mA
I_{DD}	supply current	to any supply terminal	-	±100	mA
T _{stg}	storage temperature		–65	+150	°C
T _{amb}	ambient temperature		-40	+85	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +85 ^{\circ}\text{C}$			
		DIP20 package	[2] _	750	mW
		SO20 package	[3]	500	mW
Р	power dissipation	per output	-	100	mW

^[1] See Figure 6.

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^[2] For DIP20 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

^[3] For SO20 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

Octal inverting buffers with 3-state outputs

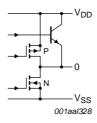
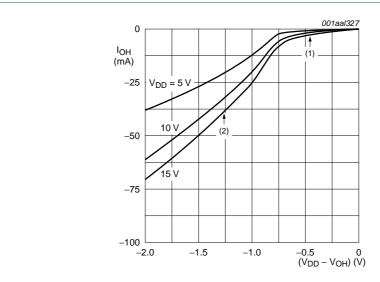


Fig 5. Schematic diagram of a buffer output stage



- (1) P-channel MOS transistor conducting.
- (2) P-channel MOS transistor and bipolar NPN transistor conducting.

Fig 6. Typical output source current characteristic

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DD}	supply voltage		3	-	15	V
VI	input voltage		0	-	V_{DD}	V
T _{amb}	ambient temperature	in free air	-40	-	+85	°C
Δt/ΔV	input transition rise and fall rate	$V_{DD} = 5 V$	-	-	3.75	μs/V
		V _{DD} = 10 V	-	-	0.5	μs/V
		V _{DD} = 15 V	-	-	0.08	μs/V

Octal inverting buffers with 3-state outputs

9. Static characteristics

Table 6. Static characteristics

 $V_{SS} = 0$ V; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T _{amb} =	T _{amb} = -40 °C		+25 °C	T _{amb} =	+85 °C	Unit
				Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$ I_{O} < 1 \mu A$	5 V	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage	$ I_{O} < 1 \mu A$	5 V	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	V
V_{H}	hysteresis voltage	for any input	5 V	-	-	-	220.0	-	-	mV
			10 V	-	-	-	250.0	-	-	mV
			15 V	-	-	-	320.0	-	-	mV
V_{OH}	HIGH-level output voltage	$ I_{O} < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage	$ I_{O} < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I _{OH}	HIGH-level output current	$V_0 = 3.6 \text{ V}$	5 V	-	-9.3	-24.0	-10.0	-	-10.7	mA
		$V_0 = 8.4 \text{ V}$	10 V	-	-14.4	-46.0	-15.0	-	-15.0	mA
		$V_0 = 13.2 \text{ V}$	15 V	-	-19.5	-62.0	-20.0	-	-19.8	mA
		$V_{O} = 4.6 \text{ V}$	5 V	-	-0.75	-1.2	-0.6	-	-0.45	mA
		$V_0 = 9.5 \ V$	10 V	-	-1.85	-3.0	-1.5	-	-1.1	mA
		$V_0 = 13.5 \text{ V}$	15 V	-	-14.5	-50.0	-15.0	-	-15.5	mA
I _{OL}	LOW-level output current	$V_0 = 0.4 \ V$	5 V	2.9	-	2.3	5.4	1.75	-	mA
		$V_0 = 0.5 \ V$	10 V	9.5	-	7.6	17.0	5.50	-	mA
		$V_0 = 1.5 \text{ V}$	15 V	30.0	-	25.0	45.0	19.0	-	mA
I	input leakage current		15 V	-	±0.3	-	±0.3	-	±1.0	μΑ
I_{DD}	supply current	I _O = 0 A	5 V	-	4	-	4	-	30	μΑ
			10 V	-	8	-	8	-	60	μΑ
			15 V	-	16	-	16	-	120	μΑ
I_{OZ}	OFF-state output current		15 V	-	1.6	-	1.6	-	12	μΑ
Cı	input capacitance		-	-	-	-	7.5	-	-	pF

Octal inverting buffers with 3-state outputs

10. Dynamic characteristics

Table 7. Dynamic characteristics

 $V_{SS} = 0 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; for test circuit see <u>Figure 10</u>; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Тур	Max	Unit
t _{PHL}	HIGH to LOW	nAn to nYn;	5 V	11 83 ns + (0.24 ns/pF)C _L	-	95	190	ns
	propagation delay	see <u>Figure 8</u>	10 V	35 ns + (0.10 ns/pF)C _L	-	40	80	ns
			15 V	26 ns + (0.07 ns/pF)C _L	-	30	60	ns
t _{PLH}	LOW to HIGH propagation delay	nAn to nYn;	5 V	11 82 ns + (0.06 ns/pF)C _L	-	85	170	ns
		see Figure 8	10 V	38 ns + (0.03 ns/pF)C _L	-	40	80	ns
			15 V	29 ns + (0.02 ns/pF)C _L	-	30	60	ns
t _{PHZ}	HIGH to OFF-state propagation delay	nOE to nYn;	5 V		-	70	140	ns
		nYn is HIGH; see <u>Figure 9</u>	10 V		-	35	70	ns
		see <u>rigure 9</u>	15 V		-	30	60	ns
t_{PLZ}	LOW to OFF-state	nOE to nYn; nYn is LOW; see <u>Figure 9</u>	5 V		-	75	150	ns
	propagation delay		10 V		-	40	80	ns
			15 V		-	30	60	ns
t _{PZH}	OFF-state to HIGH propagation delay	nOE to nYn; nYn goes HIGH; see Figure 9	5 V		-	80	160	ns
			10 V		-	35	70	ns
			15 V		-	30	60	ns
t_{PZL}	OFF-state to LOW	nOE to nYn;	5 V		-	90	180	ns
	propagation delay	nYn goes LOW; see Figure 9	10 V		-	40	80	ns
		see <u>rigure s</u>	15 V		-	30	60	ns
t_{THL}	HIGH to LOW output	see Figure 7 and	5 V		-	40	80	ns
	transition time	Figure 8	10 V		-	20	40	ns
			15 V		-	15	30	ns
t_{TLH}	LOW to HIGH output		5 V		-	30	60	ns
	transition time	Figure 8	10 V		-	20	40	ns
			15 V		-	15	30	ns

^[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

Octal inverting buffers with 3-state outputs

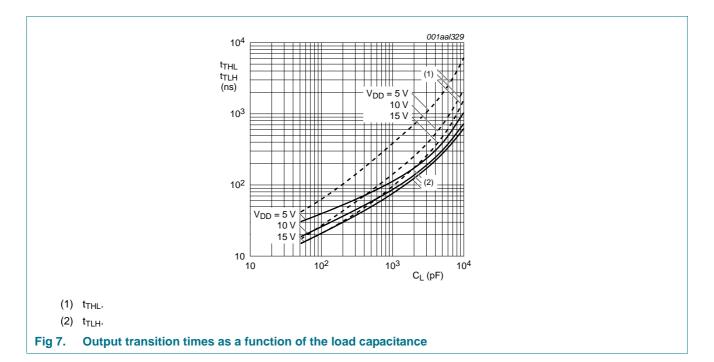


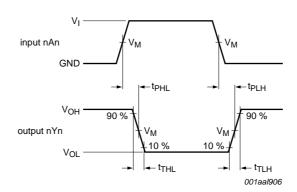
Table 8. Dynamic power dissipation P_D

 P_D can be calculated from the formulas shown. $V_{SS} = 0$ V; $t_r = t_f \le 20$ ns; $T_{amb} = 25$ °C.

Symbol	Parameter	V_{DD}	Typical formula for P _D (μW)	where:	
P_D	dynamic power	5 V	$P_D = 4250 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz,	
	dissipation	10 V	$P_D = 17000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f _o = output frequency in MHz,	
		15 V	$P_D = 46000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	C _L = output load capacitance in pF,	
				V_{DD} = supply voltage in V, $\Sigma(f_0 \times C_L)$ = sum of the outputs.	

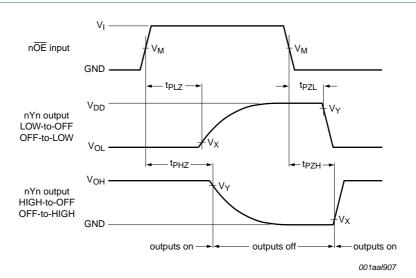
Octal inverting buffers with 3-state outputs

11. Waveforms



Measurement points are given in $\underline{\text{Table 9}}$, V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 8. Waveforms showing propagation and transition delays



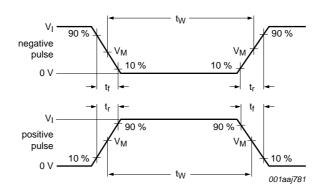
Measurement points are given in Table 9, VoL and VoH are typical output voltage levels that occur with the output load.

Fig 9. 3-state enable and disable times

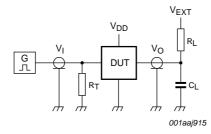
Table 9. Measurement points

Supply voltage	Input	Output		
V_{DD}	V _M	V _M	V _X	V _Y
5 V to 15 V	0.5V _{DD}	0.5V _{DD}	0.1V _{DD}	0.9V _{DD}

Octal inverting buffers with 3-state outputs



a. Input waveforms



b. Test circuit

For test data see Table 10.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance.

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 10. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V _{EXT}			
V_{DD}	VI	t _r , t _f		R _L	t _{PLH} , t _{PHL}	t _{PLZ} , t _{PZL} t _{PHZ} , t _{PZH}		
5 V to 15 V	V_{SS} or V_{DD}	\leq 20 ns	50 pF	1 kΩ	open	V_{DD}	GND	

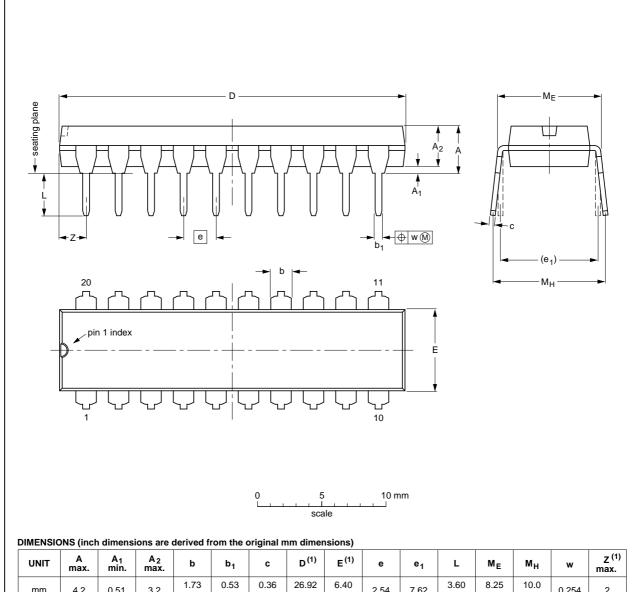
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12. Package outline

DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	0.36 0.23	26.92 26.54	6.40 6.22	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.014 0.009	1.060 1.045	0.25 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.078

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

	OUTLINE		REFER	EUROPEAN	ISSUE DATE	
	VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
	SOT146-1		MS-001	SC-603		99-12-27 03-02-13
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Fig 11. Package outline SOT146-1 (DIP20)

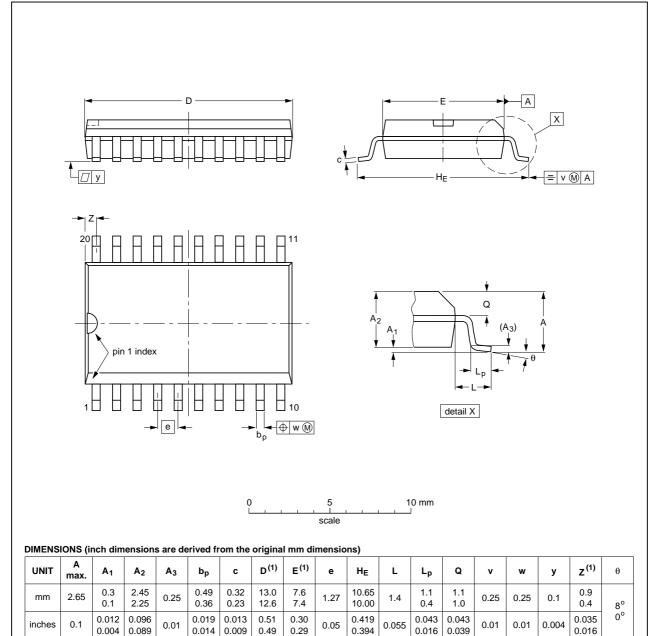
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Octal inverting buffers with 3-state outputs

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT163-1	075E04	MS-013				99-12-27 03-02-19

Fig 12. Package outline SOT163-1 (SO20)

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Octal inverting buffers with 3-state outputs

13. Abbreviations

Table 11. Abbreviations

Acronym	Description
DUT	Device Under Test
MOS	Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF40240B v.5	20111115	Product data sheet	-	HEF40240B v.4
Modifications:	 Section Appl 	lications removed		
	• Table 6: I _{OH}	minimum values changed to m	aximum	
HEF40240B v.4	20100420	Product data sheet	-	HEF40240B_CNV v.3
HEF40240B_CNV v.3	19950101	Product specification	-	HEF40240B_CNV v.2
HEF40240B_CNV v.2	19950101	Product specification	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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